

Optoelectronic Applications of Chemical Bath Deposited Cu_2SnS_3 (CTS) Thin Films

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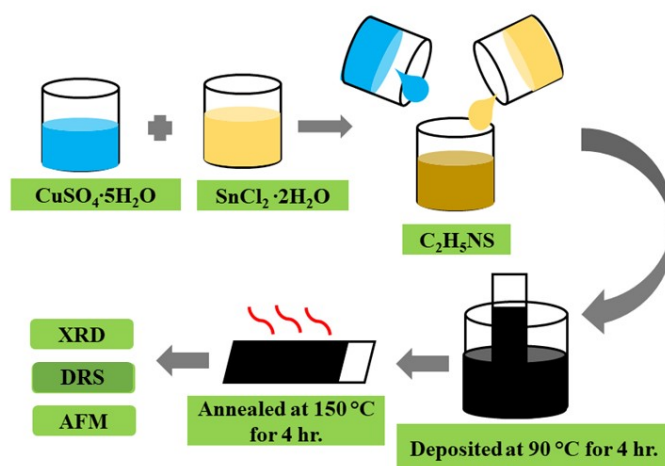


Figure S1 The schematic diagram of deposition of CTS TF by CBD method.

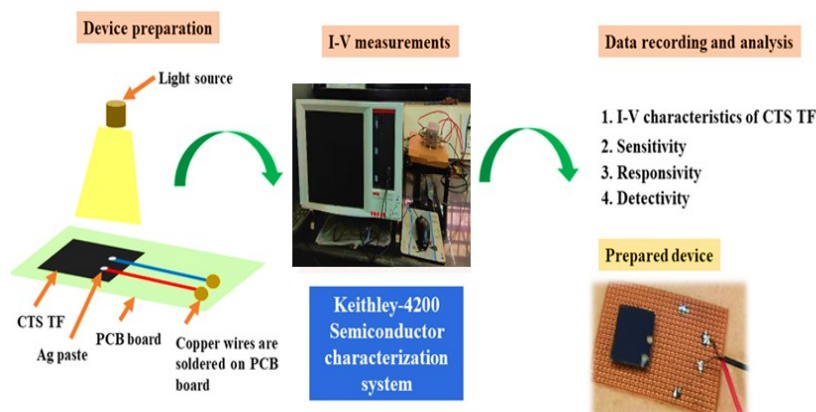


Figure S2 The device configuration for evaluating the photo-response of deposited CTS TF.

Table S1 The average and standard deviation (σ) of CTS-CdS device.

Temperature (K)	273		298		310		373	
	V _{oc} (V)	J _{sc} (mA·cm ⁻²)	V _{oc} (V)	J _{sc} (mA·cm ⁻²)	V _{oc} (V)	J _{sc} (mA·cm ⁻²)	V _{oc} (V)	J _{sc} (mA·cm ⁻²)
Thickness (μm)								
1	0.72	41	0.72	41	0.7	40.8	0.62	41.5
2	0.74	43.7	0.74	43.5	0.72	44.5	0.64	44.5
3	0.75	44.5	0.75	44.3	0.73	45	0.65	45
4	0.75	46.5	0.75	46.1	0.74	46.5	0.66	46.5
Average:	0.74	43.92	0.74	43.72	0.72	44.20	0.64	44.37
σ:	0.01	2.27	0.01	2.11	0.01	2.42	0.01	2.09

Table S2 The average and standard deviation (σ) of CTS-CdSe device.

Temperature (K)	273		298		310		373	
	V _{oc} (V)	J _{sc} (mA·cm ⁻²)	V _{oc} (V)	J _{sc} (mA·cm ⁻²)	V _{oc} (V)	J _{sc} (mA·cm ⁻²)	V _{oc} (V)	J _{sc} (mA·cm ⁻²)
Thickness (μm)								
1	0.75	43.2	0.72	42.1	0.7	42.6	0.62	42.4
2	0.77	44.1	0.74	43.0	0.72	43.9	0.64	43.7
3	0.78	45.6	0.75	45.4	0.74	45.2	0.66	46.3
4	0.78	47.00	0.75	46.7	0.74	46.7	0.66	45.3
Average:	0.77	44.97	0.74	44.52	0.725	44.60	0.64	44.42
σ:	0.01	1.67	0.01	1.98	0.02	1.75	0.02	1.72